Ordering number:EN2538A

PNP/NPN Triple Diffused Planar Type Silicon Transistors

2SB1266/2SD1902

AF Power Amplifier Applications

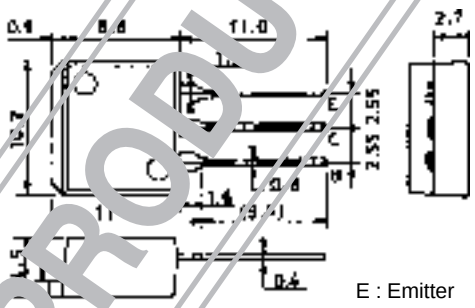
Features

- Suitable for sets whose heighit is restricted.
- Wide ASO (adoption of MBIT process).
- High reliability.

Package Dimensions

unit:mm

2049B



E : Emitter
C : Collector
B : Base
SANYO : TO-220MF

( ) : 2SB1266

Specifications

Absolute Maximum Ratings at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		(–)60	V
Collector-to-Emitter Voltage	V_{CEO}		(–)60	V
Emitter-to-Base Voltage	V_{EBO}		(–)6	V
Collector Current	I_C		(–)3	A
Collector Current (Pulse)	I_{CP}		(–)8	A
Collector Dissipation	P_C		1.65	W
		Tc=25˚C	30	W
Junction Temperature	Tj		150	˚C
Storage Temperature	Tstg		–55 to +150	˚C

Electrical Characteristics at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	V_{CB}=(–)40V, I_E=0			(–)100	μA
Emitter Cutoff Current	I_{EBO}	V_{EB}=(–)4V, I_C=0			(–)100	μA
DC Current Gain	$h_{FE}1$	V_{CE}=(–)5V, I_C=(–)0.5A	70*		280*	
	$h_{FE}2$	V_{CE}=(–)5V, I_C=(–)3A	20			
Gain-Bandwidth Product	f_T	V_{CE}=(–)5V, I_C=(–)0.5A		(8)40		MHz
Output Capacitance	C_{ob}	V_{CB}=(–)10V, f=1MHz		(60)		pF
				110		pF

* : The 2SB1266/2SD1902 are classified by 0.5A h_{FE} as follows :

70	Q	140	100	R	200	140	S	280

SANYO Electric Co.,Ltd. Semiconductor Bussiness Headquaters
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=(–)2A, I_B=(–)0.2A		(–)0.4	(–)1	V
Base-to-Emitter Voltage	V_{BE}	I_{CE}=(–)5V, I_C=(–)0.5A		(–)0.7	(–)1	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=(–)1mA, I_E=0	(–)60			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=(–)5mA, R_{BE}=∞	(–)60			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=(–)1mA, I_C=0	(–)6			V